

Tsung-Ting Kao

List of Publications by Year in descending order

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15
papers

347
citations

840776

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all docs

15
docs citations

15
times ranked

472
citing authors

#	ARTICLE	IF	CITATIONS
1	Sub 250-nm deep-UV AlGaIn/AlN distributed Bragg reflectors. Applied Physics Letters, 2017, 110, .	3.3	29
2	High-Responsivity GaN/InGaIn Heterojunction Phototransistors. IEEE Photonics Technology Letters, 2016, 28, 2035-2038.	2.5	17
3	Radiative recombination in GaN/InGaIn heterojunction bipolar transistors. Applied Physics Letters, 2015, 107, 242104.	3.3	2
4	Growth of high-quality AlN layers on sapphire substrates at relatively low temperatures by metalorganic chemical vapor deposition. Physica Status Solidi (B): Basic Research, 2015, 252, 1089-1095.	1.5	46
5	Inverse-Tapered p-Waveguide for Vertical Hole Transport in High-[Al] AlGaIn Emitters. IEEE Photonics Technology Letters, 2015, 27, 1768-1771.	2.5	9
6	GaN/InGaIn avalanche phototransistors. Applied Physics Express, 2015, 8, 032101.	2.4	20
7	Temperature-Dependent Characteristics of GaN Homo Junction Rectifiers. IEEE Transactions on Electron Devices, 2015, 62, 2679-2683.	3.0	19
8	A Remote-Oxygen-Plasma Surface Treatment Technique for III-Nitride Heterojunction Field-Effect Transistors. IEEE Transactions on Electron Devices, 2014, 61, 493-497.	3.0	16
9	Optically pumped AlGaIn quantum-well lasers at sub-250 nm grown by MOCVD on AlN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 258-260.	0.8	13
10	AlGaIn-Based Vertical Injection Laser Diodes Using Inverse Tapered p-Waveguide for Efficient Hole Transport. IEEE Journal of Quantum Electronics, 2014, 50, 166-173.	1.9	14
11	Theoretical analysis of strategies for improving p-type conductivity in wurtzite III-nitride devices for high-power optoelectronic and microelectronic applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 828-831.	0.8	4
12	Deep-ultraviolet lasing at 243-nm from photo-pumped AlGaIn/AlN heterostructure on AlN substrate. Applied Physics Letters, 2013, 102, .	3.3	77
13	Sub-250-nm low-threshold deep-ultraviolet AlGaIn-based heterostructure laser employing HfO ₂ /SiO ₂ dielectric mirrors. Applied Physics Letters, 2013, 103, .	3.3	36
14	Stimulated emission at 257-nm from optically-pumped AlGaIn/AlN heterostructure on AlN substrate. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1768-1770.	1.8	7
15	Effects of a step-graded Al _x Ga _{1-x} N electron blocking layer in InGaIn-based laser diodes. Journal of Applied Physics, 2011, 109, .	2.5	38